

WHAT IS CLAIMED IS:

1. An oscillator circuit comprising:

a CR circuit for providing a feedback circuit to an active device, wherein the CR circuit is comprised of a first resistor group and a capacitor; and

a second resistor group comprised of one or more resistors, wherein the second resistor group is for adjusting a charge/discharge trigger voltage and a charge/discharge time associated with the capacitor of the CR circuit, wherein the second resistor group has a temperature coefficient that is larger than a temperature coefficient associated with the first resistor group.

2. The oscillator circuit of claim 1, wherein the first resistor group and the second resistor group are semiconductor resistor elements.

3. The oscillator circuit of claim 2, wherein the temperature coefficients of the first resistor group and the second resistor group are varied by changing an impurity density of the semiconductor resistor elements.

4. The oscillator circuit of claim 2, wherein the semiconductor resistor elements are comprised of impurity doped polysilicon resistor or diffused resistor.

5. The oscillator circuit of claim 1, wherein the oscillator circuit is integrated in one chip.

6. An oscillator circuit comprising:

a plurality of inverters comprised of more than three inverters connected in series;

a feedback path connected from an output terminal of an odd number inverter of the plurality of inverters through a first resistor to an input terminal of the first inverter of the more than three inverters; and

another feedback path connected from an output terminal of an even numbered inverter of the plurality of inverters through a capacitor and a second resistor to the input terminal of the first inverter,

wherein the second resistor has a temperature coefficient larger than a temperature coefficient of the first resistor.

7. The oscillator circuit of claim 6, wherein the first resistor and the second resistor are semiconductor resistor elements.

8. The oscillator circuit of claim 7, wherein the temperature coefficients of the first resistor and the second resistor are varied by changing an impurity density of the semiconductor resistor elements.

9. The oscillator circuit of claim 7, wherein the semiconductor resistor elements are comprised of impurity doped polysilicon resistor or diffused resistor.

10. The oscillator circuit of claim 7, wherein the oscillator circuit is integrated in one chip.

11. An oscillator circuit comprising:

a CR circuit comprised of a capacitor and a resistor, wherein the CR circuit is coupled to an input terminal of a comparator; and

a divider comprised of a plurality of resistors, wherein the divider applies a voltage to another input terminal of the comparator after the voltage has been divided by the plurality of resistors, wherein:

a first group of resistors among the plurality of resistors has a temperature coefficient larger than a temperature coefficient of the other resistor of the plurality of resistors; and

the temperature coefficient of the first group of resistors is also larger than a temperature coefficient of the resistor of the CR circuit.

12. The oscillator circuit of claim 11, wherein the resistor of the CR circuit and the plurality of resistors of the divider are semiconductor resistor elements.

13. The oscillator circuit of claim 12, wherein the temperature coefficient of the resistor of the CR circuit and the temperature coefficient of the plurality of resistors of the divider are varied by changing an impurity density of the semiconductor resistor elements.

14. The oscillator circuit of claim 12, wherein the semiconductor resistor elements are comprised of impurity doped polysilicon resistor or diffused resistor.

15. The oscillator circuit of claim 12, wherein the oscillator circuit is integrated in one chip.